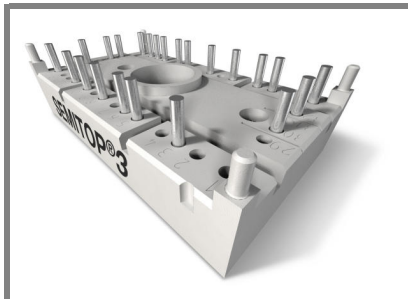


# SK50MLI065



SEMITOP® 3

## IGBT Module

SK50MLI065

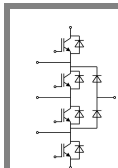
### Target Data

### Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Ultra Fast NPT IGBT technology
- CAL technology FWD

### Typical Applications\*

- Multi level inverter



MLI

Absolute Maximum Ratings		$T_s = 25^\circ\text{C}$ , unless otherwise specified	
Symbol	Conditions	Values	Units
<b>IGBT</b>			
$V_{CES}$	$T_j = 25^\circ\text{C}$	600	V
$I_C$	$T_j = 125^\circ\text{C}$	$T_s = 25^\circ\text{C}$	54 A
		$T_s = 80^\circ\text{C}$	40 A
$I_{CRM}$	$I_{CRM} = 2 \times I_{Cnom}$	120	A
$V_{GES}$		$\pm 20$	V
$t_{psc}$	$V_{CC} = 300\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125^\circ\text{C}$ $V_{CES} < 600\text{ V}$	10	$\mu\text{s}$

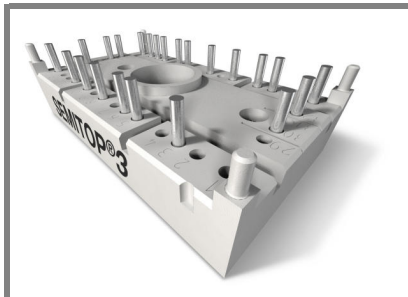
Inverse Diode		$T_s = 25^\circ\text{C}$ , unless otherwise specified	
Symbol	Conditions	Values	Units
$I_F$	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	36 A
		$T_s = 80^\circ\text{C}$	24 A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$		A
$I_{FSM}$	$t_p = 10\text{ ms}; \text{half sine wave}$ $T_j = 150^\circ\text{C}$	200	A

Freewheeling Diode		$T_s = 25^\circ\text{C}$ , unless otherwise specified	
Symbol	Conditions	Values	Units
$I_F$	$T_j = 150^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$	64 A
		$T_{case} = 80^\circ\text{C}$	42 A
$I_{FRM}$			A
$I_{FSM}$	$t_p = 10\text{ ms}; \text{half sine wave}$ $T_j = 150^\circ\text{C}$	440	A

Module		$T_s = 25^\circ\text{C}$ , unless otherwise specified	
Symbol	Conditions	Values	Units
$I_{t(RMS)}$			A
$T_{vj}$		-40 ... +150	$^\circ\text{C}$
$T_{stg}$		-40 ... +125	$^\circ\text{C}$
$V_{isol}$	AC, 1 min.	2500	V

Characteristics		$T_s = 25^\circ\text{C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
<b>IGBT</b>					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 1,4\text{ mA}$	3	4	5	V
$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$ $T_j = 25^\circ\text{C}$			0,0044	mA
$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$ $T_j = 25^\circ\text{C}$			240	nA
$V_{CE0}$				$T_j = 25^\circ\text{C}$	1,4 V
				$T_j = 125^\circ\text{C}$	1,7 V
$r_{CE}$	$V_{GE} = 15\text{ V}$			$T_j = 25^\circ\text{C}$	m $\Omega$
				$T_j = 125^\circ\text{C}$	22 m $\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 60\text{ A}, V_{GE} = 15\text{ V}$			$T_j = 25^\circ\text{C}_{chiplev.}$	1,8 V
				$T_j = 125^\circ\text{C}_{chiplev.}$	2,1 V
$C_{ies}$	$V_{CE} = 25, V_{GE} = 0\text{ V}$ $f = 1\text{ MHz}$				3,2 nF
$C_{oes}$				0,3 nF	
$C_{res}$				0,18 nF	
$t_{d(on)}$	$R_{Gon} = 15\ \Omega$	$V_{CC} = 300\text{ V}$ $I_C = 40\text{ A}$			60 ns
$t_r$					30 ns
$E_{on}$	$R_{Goff} = 15\ \Omega$	$T_j = 125^\circ\text{C}$ $V_{GE} = \pm 15\text{ V}$			1,07 mJ
$t_{d(off)}$					223 ns
$t_f$					20 ns
$E_{off}$					0,76 mJ
$R_{th(j-s)}$	per IGBT			0,85	K/W

# SK50MLI065



SEMITOP® 3

## IGBT Module

SK50MLI065

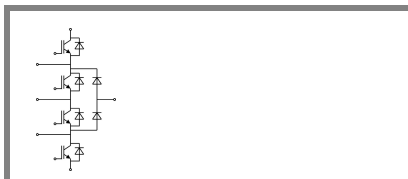
### Target Data

### Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Ultra Fast NPT IGBT technology
- CAL technology FWD

### Typical Applications\*

- Multi level inverter

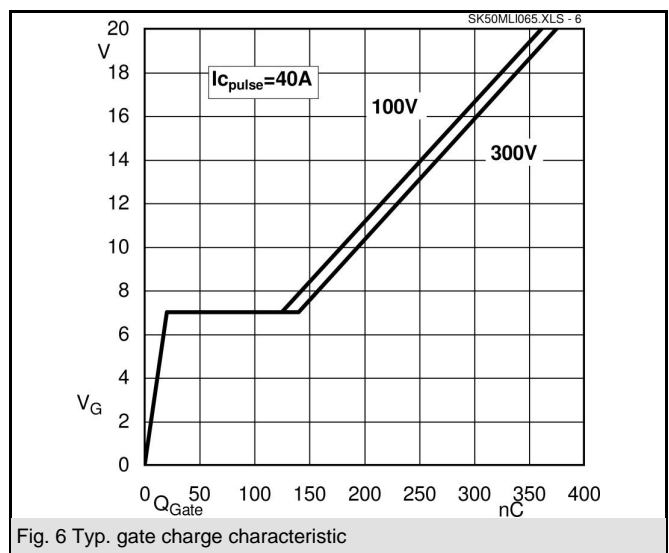
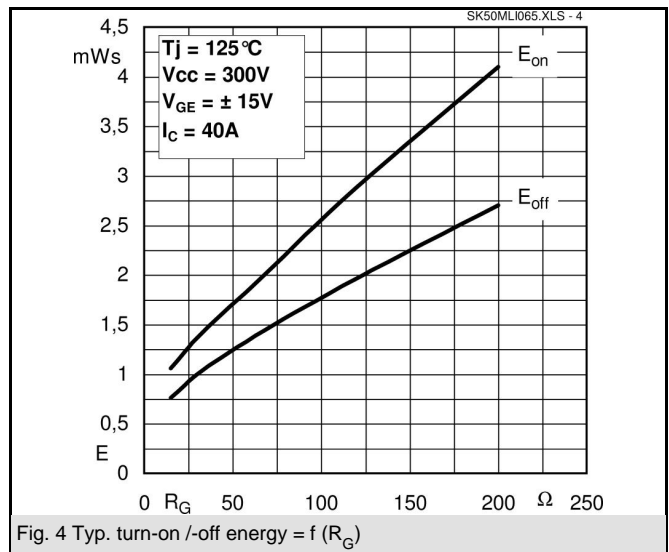
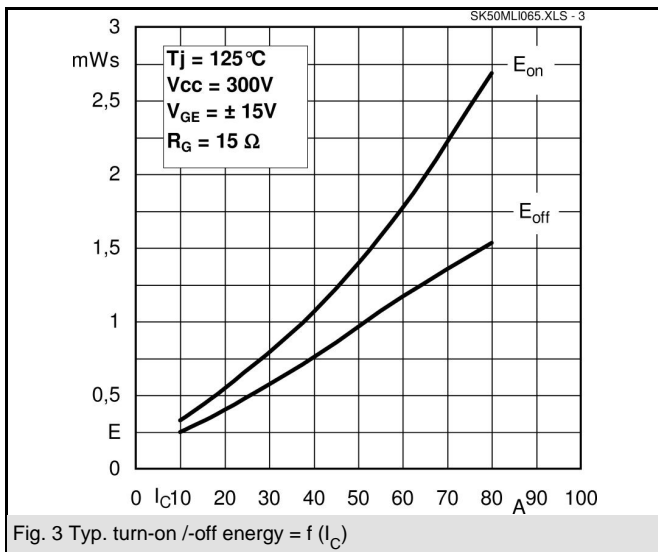
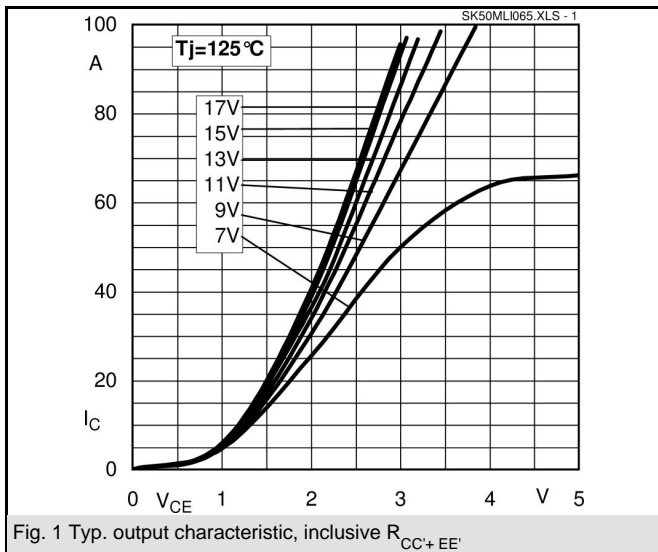


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Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
<b>Antiparallel Diode (D1)</b>					
$V_F = V_{EC}$	$I_{Fnom} = 25 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	1,45		V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$	1,4		V
$V_{F0}$		$T_j = 25 \text{ }^\circ\text{C}$			V
		$T_j = 125 \text{ }^\circ\text{C}$	0,85		V
$r_F$		$T_j = 25 \text{ }^\circ\text{C}$			mΩ
		$T_j = 125 \text{ }^\circ\text{C}$	22		mΩ
$I_{RRM}$	$I_F = 50 \text{ A}$	$T_j = 125 \text{ }^\circ\text{C}$			A
$Q_{rr}$	$di/dt = -2400 \text{ A}/\mu\text{s}$				μC
$E_{rr}$	$V_R = 300\text{V}$				mJ
$R_{th(j-s)D}$	per diode			1,7	K/W
<b>Freewheeling Diode (D2)</b>					
$V_F = V_{EC}$	$I_{Fnom} = 50 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	1,45		V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$	1,4		V
$V_{F0}$		$T_j = 125 \text{ }^\circ\text{C}$	0,85		V
$r_F$		$T_j = 125 \text{ }^\circ\text{C}$	11		V
$I_{RRM}$	$I_F = 50 \text{ A}$	$T_j = 125 \text{ }^\circ\text{C}$			A
$Q_{rr}$	$di/dt = -2400 \text{ A}/\mu\text{s}$				μC
$E_{rr}$	$V_R = 300\text{V}$				mJ
$R_{th(j-s)FD}$	per diode			1,1	K/W
$M_s$	to heat sink		2,25	2,5	Nm
w			30		g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



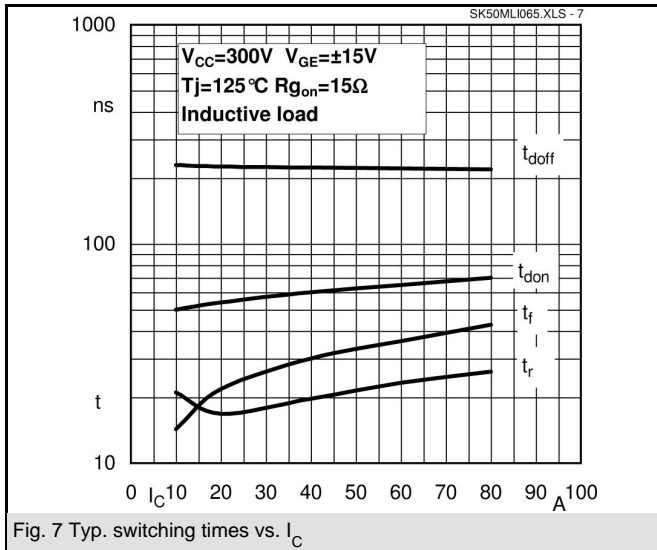


Fig. 7 Typ. switching times vs.  $I_C$

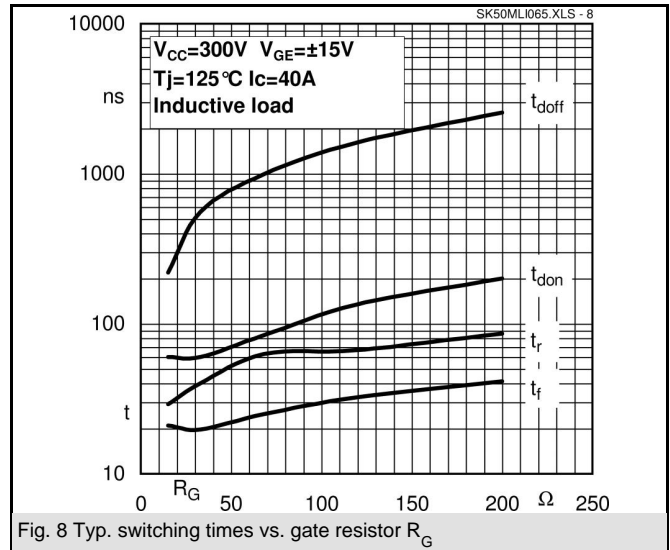


Fig. 8 Typ. switching times vs. gate resistor  $R_G$

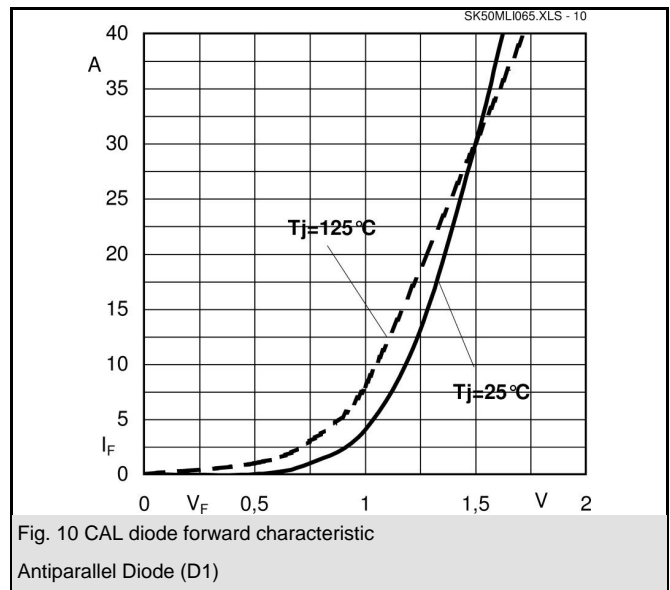
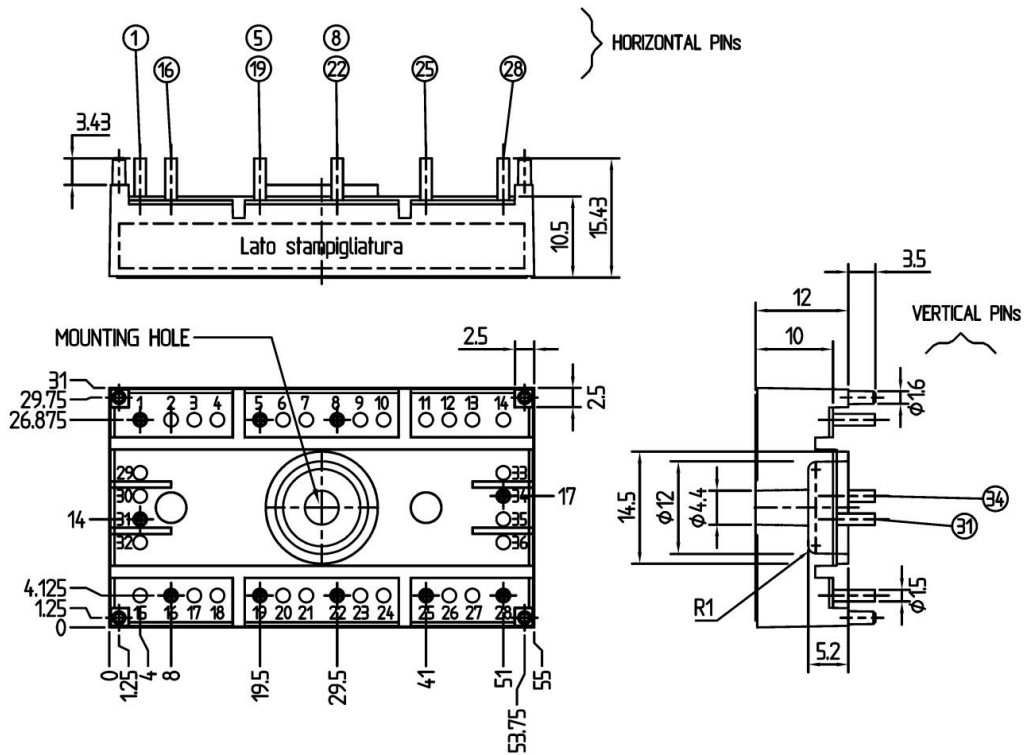


Fig. 10 CAL diode forward characteristic  
 Antiparallel Diode (D1)

# SK50MLI065

UL recognized file

no. E 63 532



Case T 76 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)

